

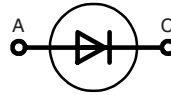
HiPerFRED™ Epitaxial Diode with soft recovery

$$I_{FAV} = 30 \text{ A}$$

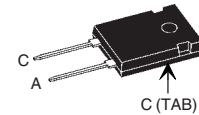
$$V_{RRM} = 1200 \text{ V}$$

$$t_{rr} = 40 \text{ ns}$$

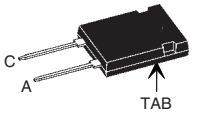
V_{RSM} V	V_{RRM} V	Type
1200	1200	DSEP 30-12A
1200	1200	DSEP 30-12AR



TO-247 AD
Version A



ISOPLUS 247™
Version AR



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}	rectangular, d = 0.5; T_C (Vers. A) = 115°C T_C (Vers. AR) = 110°C	70	A
I_{FAVM}		30	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	200	A
E_{AS}	$T_{VJ} = 25^\circ\text{C}$; non-repetitive $I_{AS} = 11.5 \text{ A}$; $L = 180 \mu\text{H}$	14	mJ
I_{AR}	$V_A = 1.25 \cdot V_R$ typ.; $f = 10 \text{ kHz}$; repetitive	1.2	A
T_{VJ}		-55...+175	°C
T_{VJM}		175	°C
T_{stg}		-55...+150	°C
P_{tot}	$T_C = 25^\circ\text{C}$	165	W
M_d^*	mounting torque	0.8...1.2	Nm
F_C	mounting force with clip	20...120	N
V_{ISOL}^{**}	50/60 Hz RMS; $I_{ISOL} \leq 1 \text{ mA}$; leads-to-tab	2500	V~
Weight	typical	6	g

* Version A only; ** Version AR only

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$; $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$; $V_R = V_{RRM}$	250 1	μA mA
V_F ②	$I_F = 30 \text{ A}$; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.79 2.74	V V
R_{thJC}	Version A	0.9	K/W
R_{thCH}	Version AR	1.1	K/W
		0.25	K/W
t_{rr}	$I_F = 1 \text{ A}$; $-di/dt = 200 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	40	ns
I_{RM}	$V_R = 100 \text{ V}$; $I_F = 50 \text{ A}$; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	8.5	11.4 A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%
② Pulse Width = 300 μs , Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified.

Features

- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0
- Version ..R isolated and UL registered E153432

Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Dimensions see Outlines.pdf

IXYS reserves the right to change limits, test conditions and dimensions.

© 2005 IXYS All rights reserved

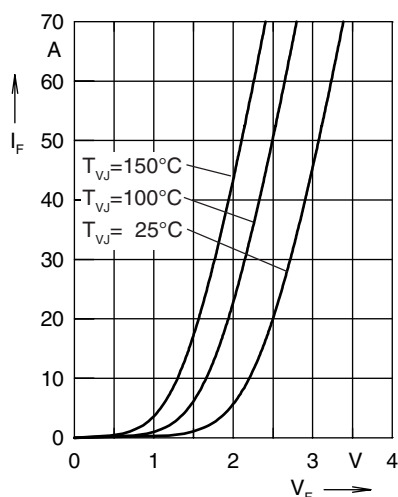


Fig. 1 Forward current I_F versus V_F

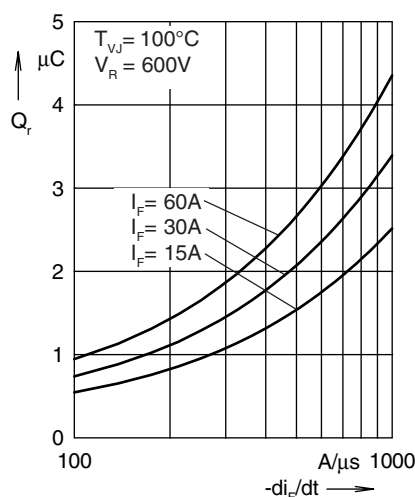


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

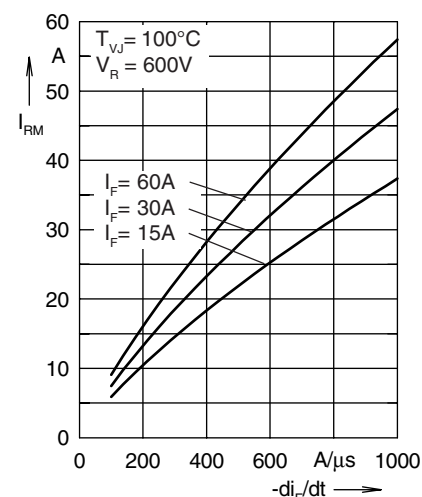


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

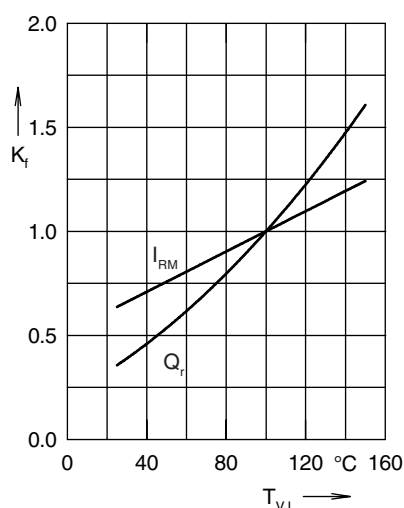


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

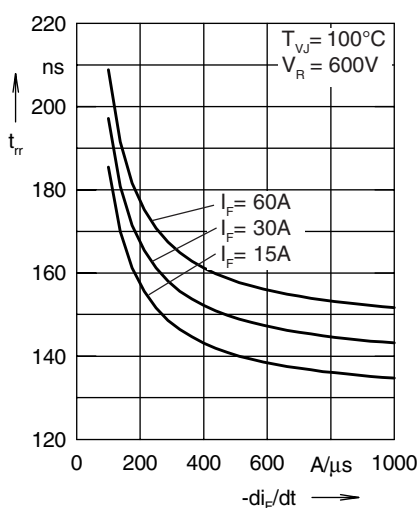


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

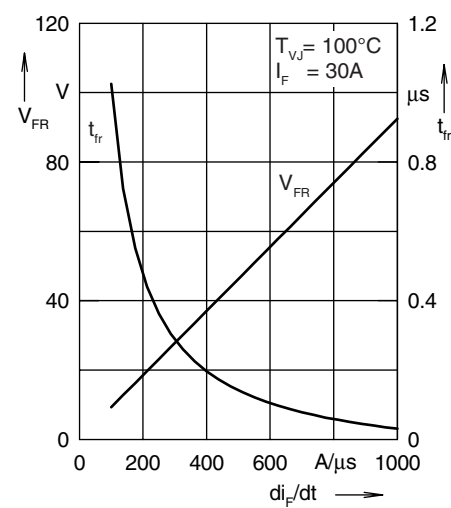


Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

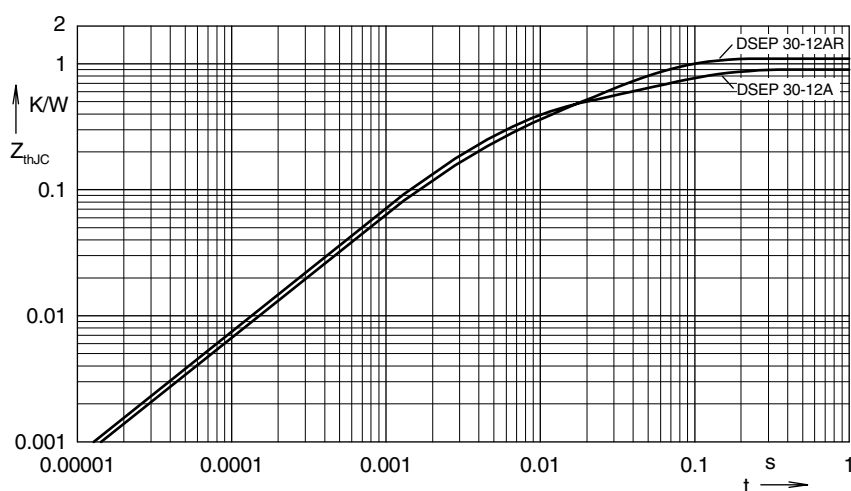


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation ..A:

i	R_{thi} (K/W)	t_i (s)
1	0.465	0.0052
2	0.179	0.0003
3	0.256	0.0397

Constants for Z_{thJC} calculation ..AR:

i	R_{thi} (K/W)	t_i (s)
1	0.368	0.0052
2	0.1417	0.0003
3	0.0295	0.0004
4	0.5604	0.0092

NOTE: Fig. 2 to Fig. 6 shows typical values